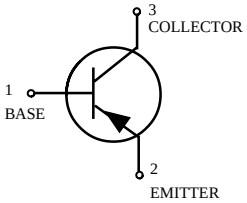
General Purpose Transistors

PNP Silicon

- We declare that the material of product compliance with RoHS requirements.

Purpose: General amplifier and switching application.
Features: Excellent h_{FE} linearity, complementary pair with FTC3876.

SOT-23



Absolute maximum ratings(Ta=25℃)

Symbol	Rating	Unit
V_{CBO}	-35	V
V_{CEO}	-30	V
V_{EBO}	-5.0	V
I_C	-500	mA
I_B	-50	mA
P_C	150	mW
T_j	150	℃
T_{stg}	-55～150	℃

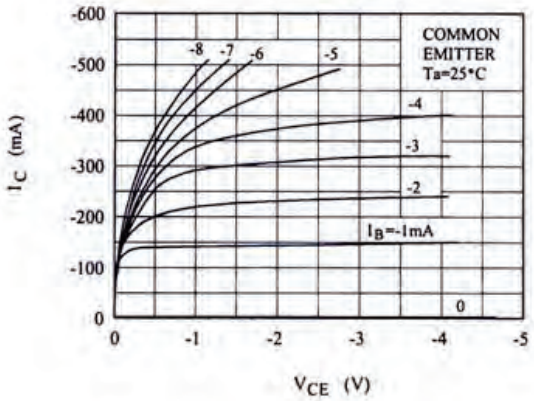
Electrical characteristics(Ta=25℃)

Symbol	Test condition	Rating			Unit
		Min	Typ	Max	
I_{CBO}	V_{CB}=-35V I_E=0			-0.1	μA
I_{EBO}	V_{EB}=-5.0V I_C=0			-0.1	μA
$h_{FE(1)}$	V_{CE}=-1.0V I_C=-100mA	70		400	
$h_{FE(2)}$	V_{CE}=-6.0V I_C=-400mA	25			
$V_{CE(sat)}$	I_C=-100mA I_B=-10mA		-0.1	-0.25	V
V_{BE}	V_{CE}=-1.0V I_C=-100mA		-0.8	-1.0	V
f_T	V_{CE}=-6.0V I_C=-20mA		200		MHz
C_{ob}	V_{CB}=-6.0V I_E=0 f=1.0MHz		13		pF

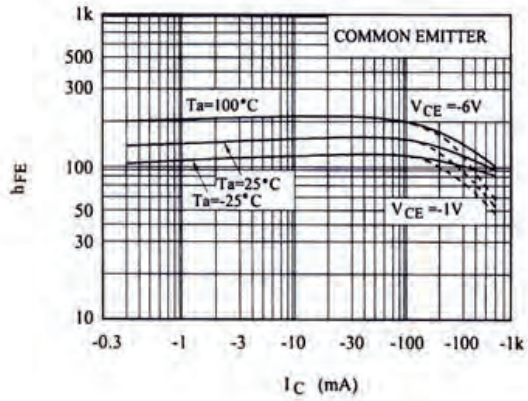
$h_{FE(1)}$ classifications、Marking:

$h_{FE(1)}$ Classifications	O	Y	GR
$h_{FE(1)}$ Range	70～140	120～240	200～400
Marking	HAZO	HAZY	HAZG

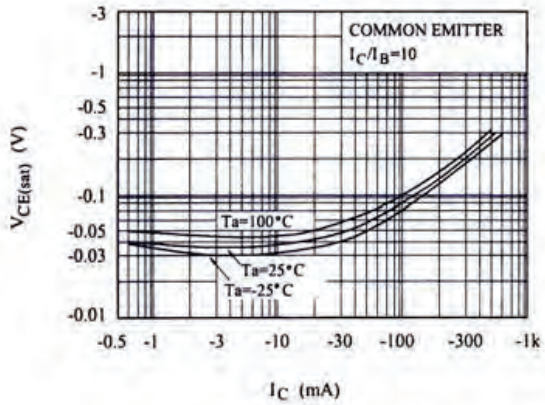
I_C - V_{CE}



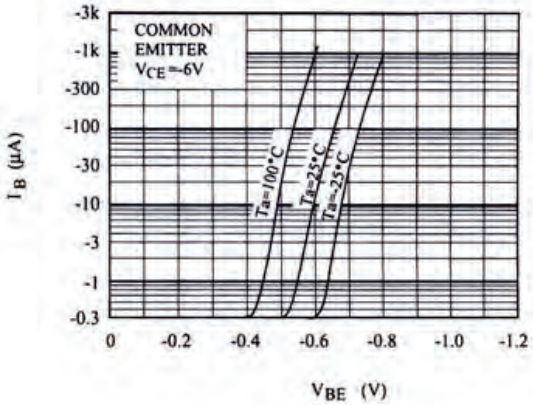
h_{FE} - I_C



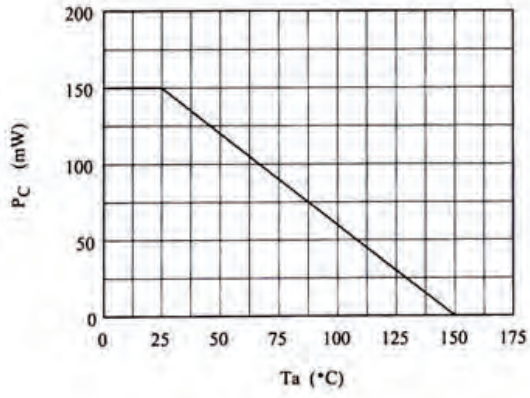
$V_{CE(sat)}$ - I_C



I_B - V_{BE}



P_C - Ta



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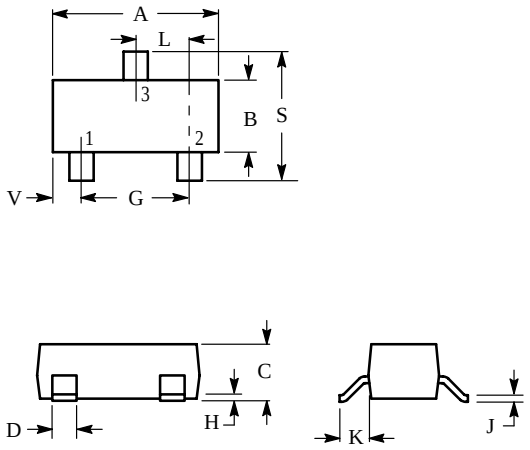

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60